



THE DATASHEET OF IRFU3412PBF



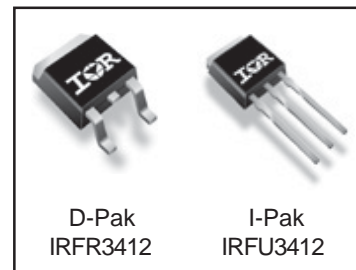
Applications

- Switch Mode Power Supply (SMPS)
- Motor Drive
- Bridge Converters
- All Zero Voltage Switching
- Lead-Free

V_{DSS}	R_{DS(on)} max	I_D
100V	0.025Ω	48A Ⓞ

Benefits

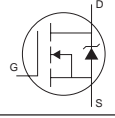
- Low Gate Charge Q_g results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Enhanced Body Diode dv/dt Capability



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	48Ⓞ	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	34Ⓞ	
I _{DM}	Pulsed Drain Current Ⓞ	190	
P _D @ T _C = 25°C	Power Dissipation	140	W
	Linear Derating Factor	0.95	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt Ⓞ	6.4	V/ns
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 second	300(1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	48Ⓞ	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) Ⓞ	—	—	190		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 29A, V _{GS} = 0V Ⓞ
t _{rr}	Reverse Recovery Time	—	68	100	ns	T _J = 125°C, I _F = 29A di/dt = 100A/μs Ⓞ
Q _{rr}	Reverse Recovery Charge	—	160	240	nC	
I _{RRM}	Reverse Recovery Current	—	4.5	6.8	A	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

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Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.10	—	V/°C	Reference to 25°C, I _D = 1mA ⑥
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.025	Ω	V _{GS} = 10V, I _D = 29A ④
V _{GS(th)}	Gate Threshold Voltage	3.5	—	5.5	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V _{DS} = 95V, V _{GS} = 0V
		—	—	250		V _{DS} = 80V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V

Dynamic @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	25	—	—	S	V _{DS} = 50V, I _D = 29A
Q _g	Total Gate Charge	—	59	89	nC	I _D = 29A
Q _{gs}	Gate-to-Source Charge	—	21	32		V _{DS} = 50V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	17	26		V _{GS} = 10V, ④
t _{d(on)}	Turn-On Delay Time	—	19	—	ns	V _{DD} = 50V
t _r	Rise Time	—	68	—		I _D = 29A
t _{d(off)}	Turn-Off Delay Time	—	44	—		R _G = 6.8Ω
t _f	Fall Time	—	37	—		V _{GS} = 10V ④
C _{iss}	Input Capacitance	—	3430	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	270	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	150	—		f = 1.0MHz
C _{oss}	Output Capacitance	—	1040	—		V _{GS} = 0V, V _{DS} = 1.0V, f = 1.0MHz
C _{oss}	Output Capacitance	—	170	—		V _{GS} = 0V, V _{DS} = 80V, f = 1.0MHz
C _{oss eff.}	Effective Output Capacitance	—	270	—		V _{GS} = 0V, V _{DS} = 0V to 80V ⑤

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy②	—	160	mJ
I _{AR}	Avalanche Current①	—	29	A
E _{AR}	Repetitive Avalanche Energy①	—	14	mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	1.05	°C/W
R _{θJA}	Junction-to-Ambient (PCB mount)*	—	50	
R _{θJA}	Junction-to-Ambient	—	110	

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11)
- ② Starting T_J = 25°C, L = 0.38mH, R_G = 25Ω, I_{AS} = 29A, (See Figure 12a)
- ③ I_{SD} ≤ 29A, di/dt ≤ 420A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ C_{oss eff.} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DS}
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.

* When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994

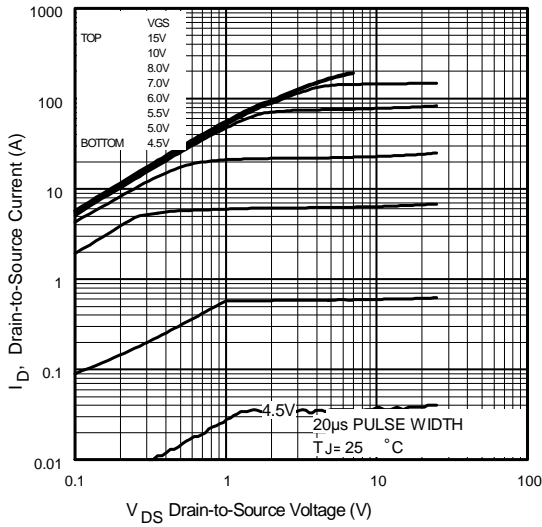


Fig 1. Typical Output Characteristics

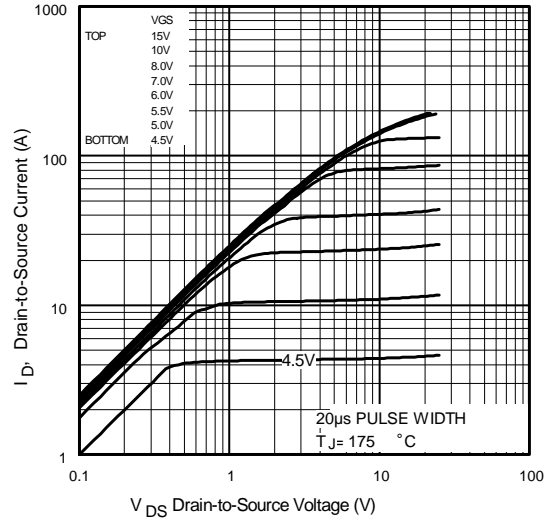


Fig 2. Typical Output Characteristics

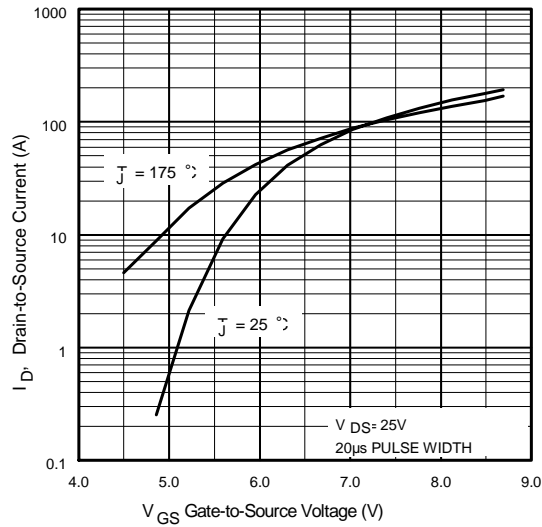


Fig 3. Typical Transfer Characteristics

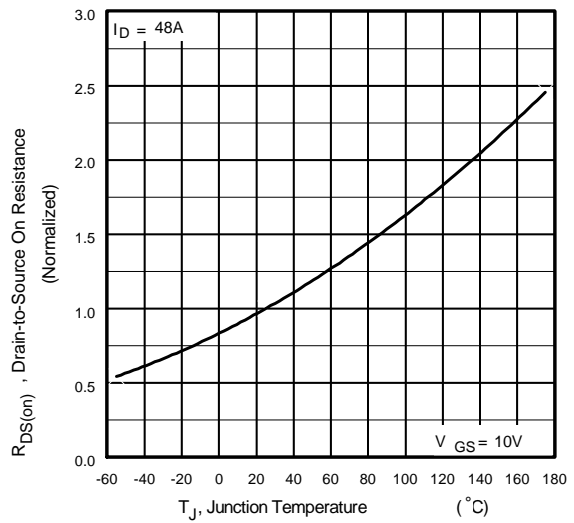


Fig 4. Normalized On-Resistance Vs. Temperature

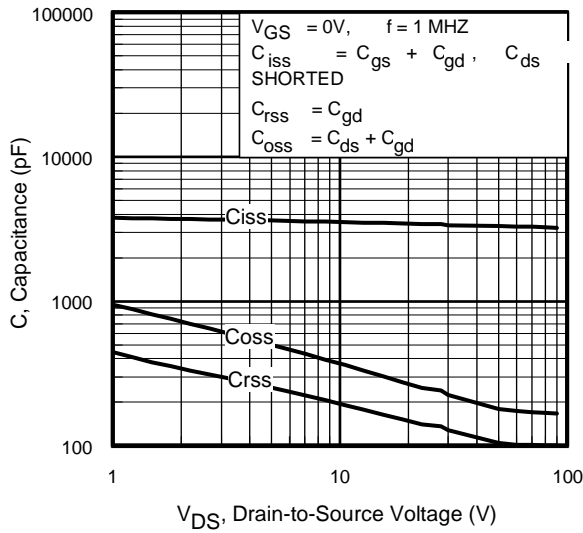


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

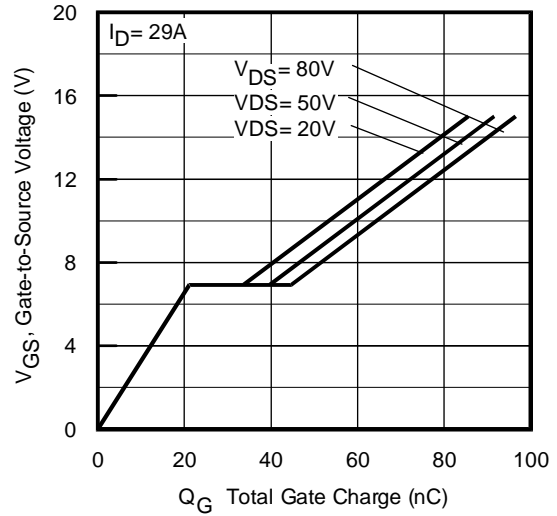


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

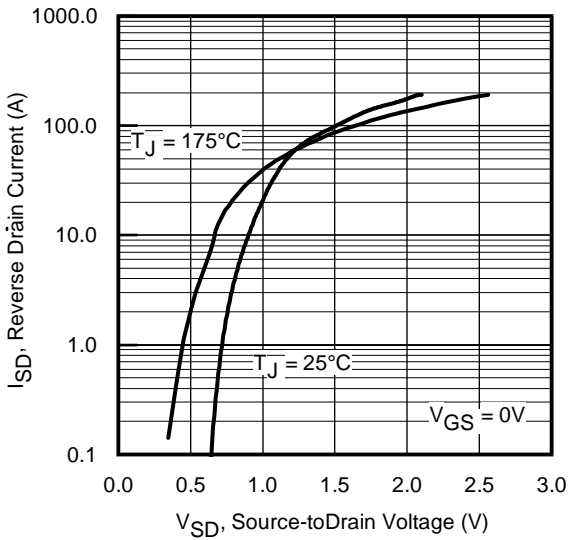


Fig 7. Typical Source-Drain Diode Forward Voltage

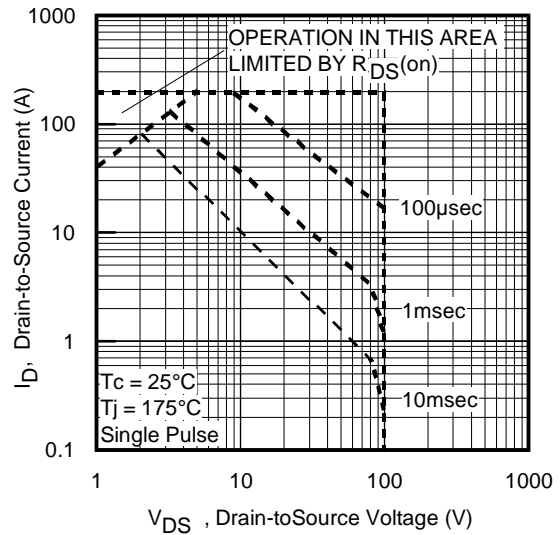


Fig 8. Maximum Safe Operating Area

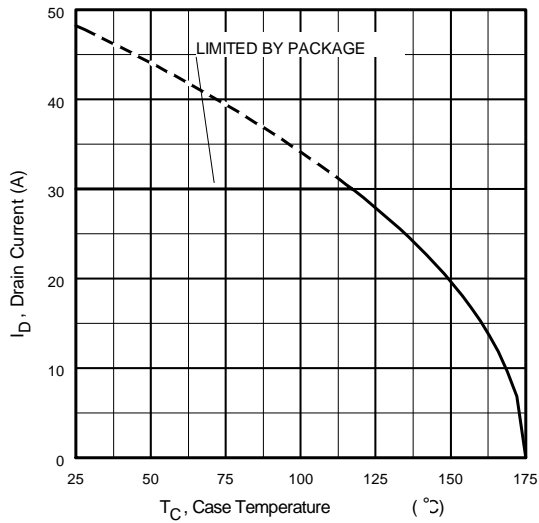


Fig 9. Maximum Drain Current Vs. Case Temperature

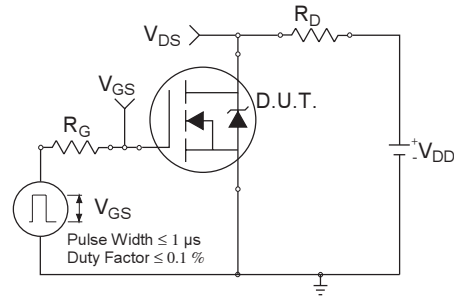


Fig 10a. Switching Time Test Circuit



Fig 10b. Switching Time Waveforms

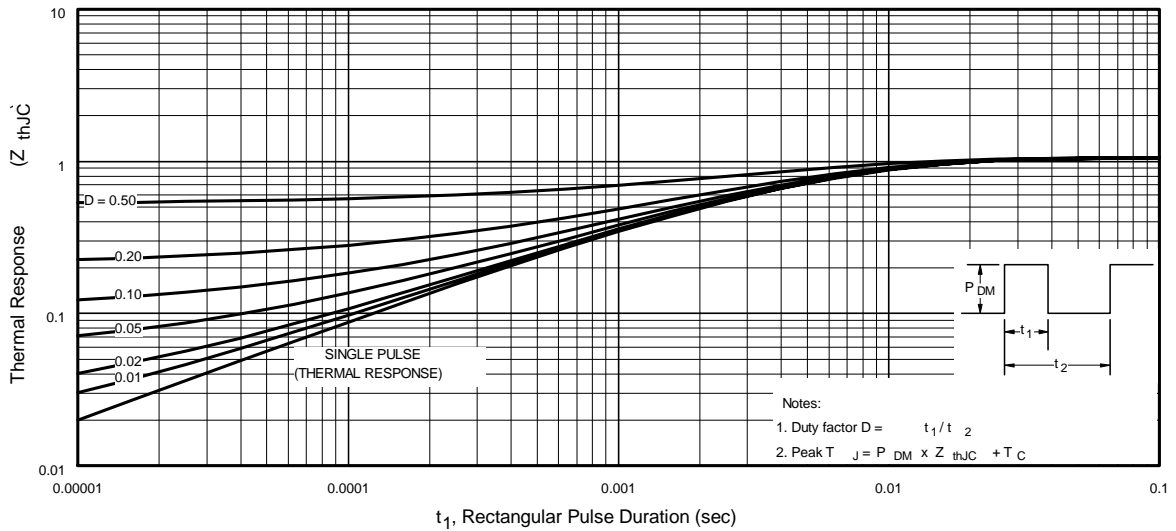


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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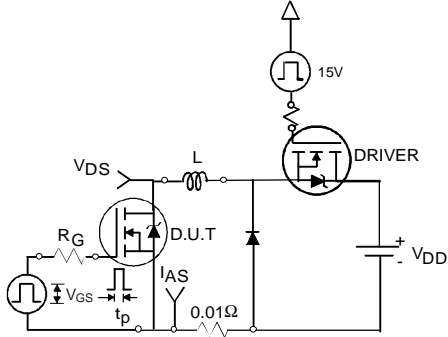


Fig 12a. Unclamped Inductive Test Circuit

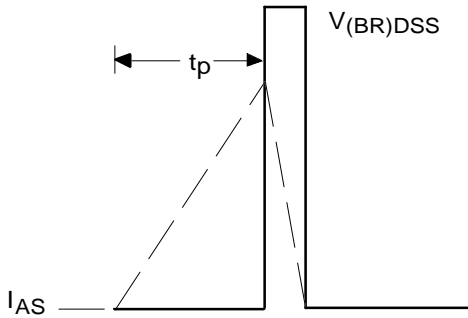


Fig 12b. Unclamped Inductive Waveforms

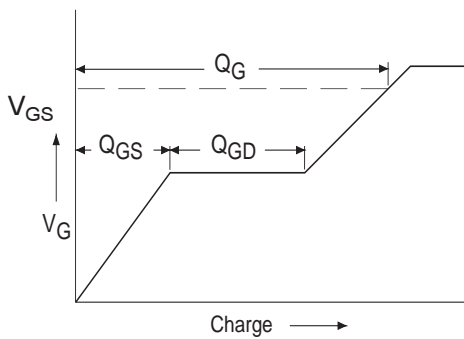


Fig 13a. Basic Gate Charge Waveform

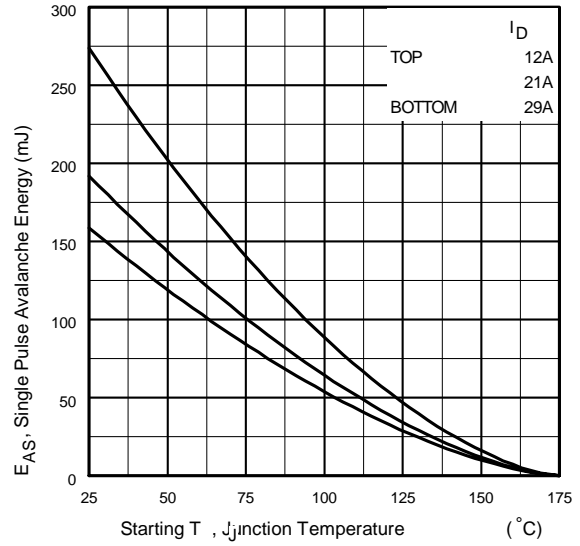


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

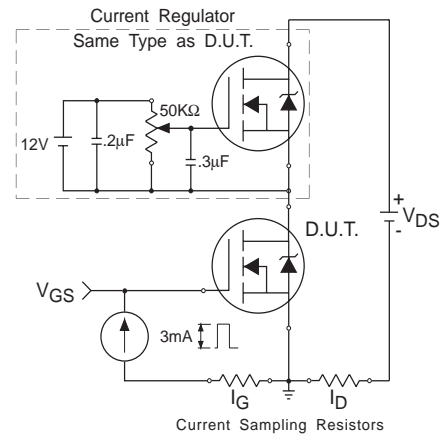


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

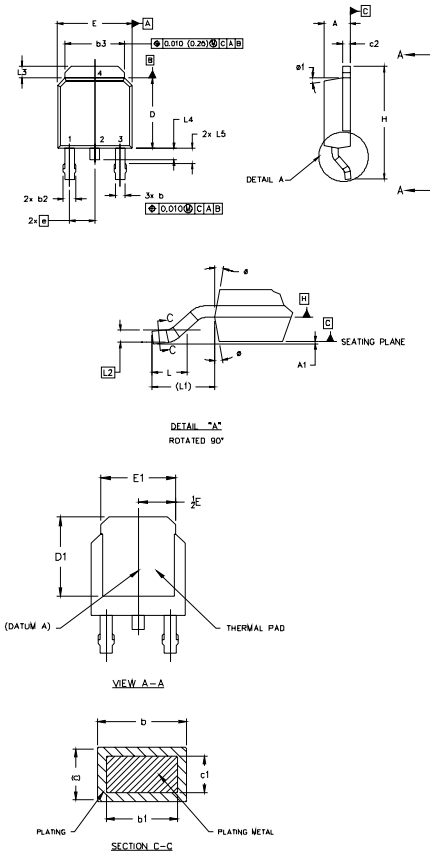


* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFET® Power MOSFETs

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D-Pak (TO-252AA) Package Outline



- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
 - 2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
 - 3.0 LEAD DIMENSION UNCONTROLLED IN L5.
 - 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
 - 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.2540] FROM THE LEAD TIP.
 - 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 - 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1		0.13		.005	
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	.031	5
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.046	0.89	.018	.035	5
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 REF		.108 REF		
L2	0.051 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	
L4		1.02		.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

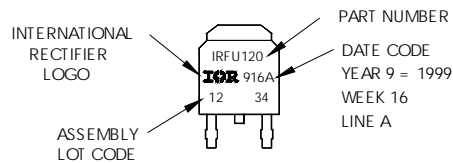
IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

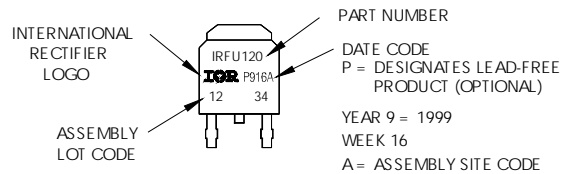
D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON VW16, 1999
IN THE ASSEMBLY LINE "A"

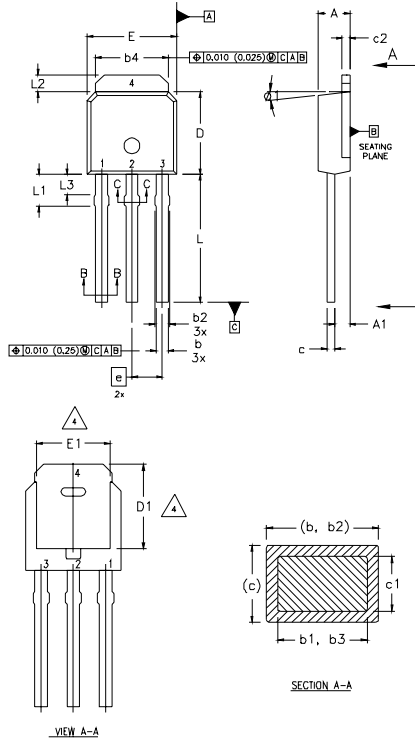
Note: "P" in assembly line position
indicates "Lead-Free"



OR



I-Pak (TO-251AA) Package Outline Dimensions are shown in millimeters (inches)



NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

LEAD ASSIGNMENTS

HEXFET

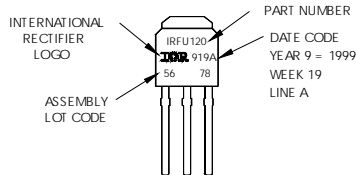
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.260	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	Ø	15°	Ø	15°	

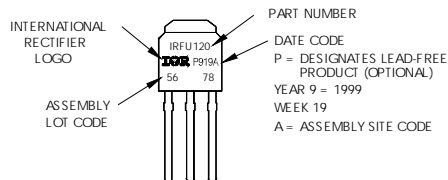
I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line
position indicates "Lead-Free"



OR

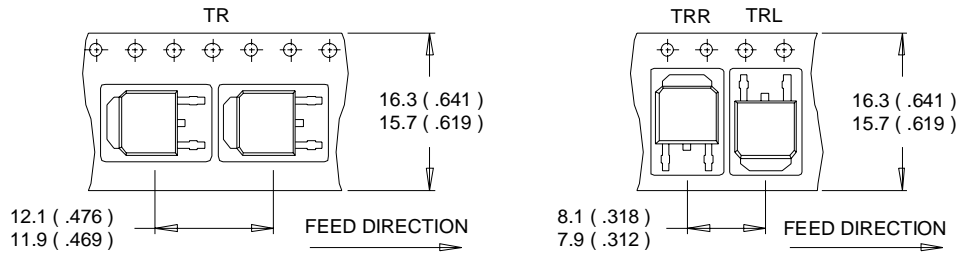


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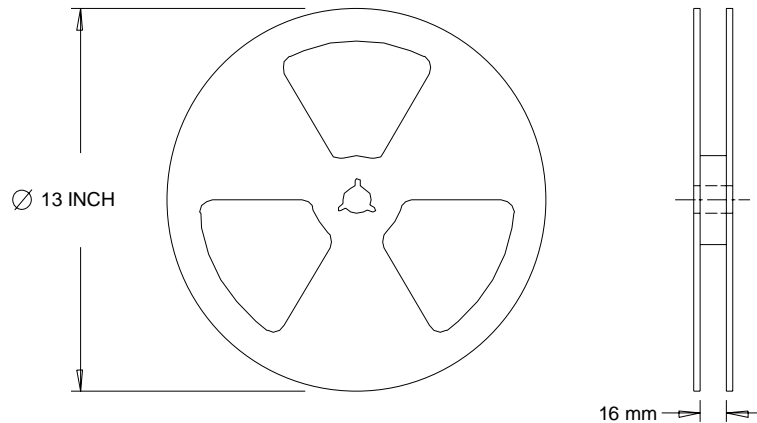
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

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TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.12/04

www.irf.com

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>

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-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management